

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

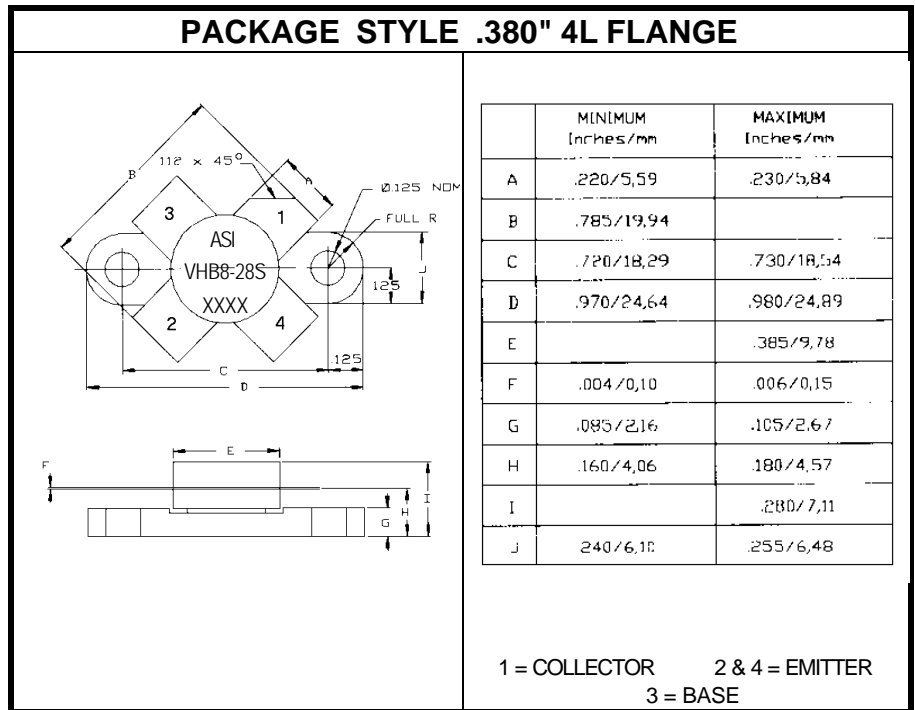
The **ASI VHB8-28F** is Designed for 28 V Large Signal Class C Amplifier Applications up to 175 MHz.

FEATURES INCLUDE:

- Emitter Ballasting
- Gold Metalization
- 3/8" SOE Flange Package

MAXIMUM RATINGS

I_C	1.0 A
V_{CE}	35 V
V_{CB}	65 V
P_{DISS}	15 W @ T _C = 25 °C
T_J	-65 °C to + 200 °C
T_{STG}	-65 °C to + 150 °C
q_{JC}	11.7 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 200 mA	65			V
BV_{CEO}	I _C = 200 mA	35			V
BV_{EBO}	I _E = 5 mA	4.0			V
I_{CB0}	V _{CB} = 30 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	5.0			---
C_{OB}	V _{CB} = 30 V f = 1.0 MHz			15	pF
P_G	V _{CC} = 28 V P _{OUT} = 8.0 W f = 175 MHz	12.0	13.0		dB
h_c		60			%